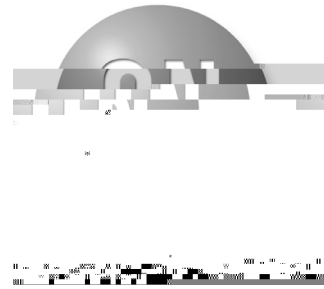


MBD701, MMBD701L, SMMBD701L



Silicon Hot-Carrier Diodes Schottky Barrier Diodes

These devices are designed primarily for high-efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low-cost, high-volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

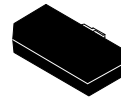
Features

- Extremely Low Minority Carrier Lifetime – 15 ps (Typ)
- Very Low Capacitance – 1.0 pF @ $V_R = 20$ V
- High Reverse Voltage – to 70 V
- Low Reverse Leakage – 200 nA (Max)
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	V
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ MBD701 MMBD701L, SMMBD701L	P_F	280 200	mW
Derate above 25°C MBD701 MMBD701L, SMMBD701L		2.8 2.0	mW/ $^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



SOT-23 (TO-236)
CASE 318
STYLE 8

MBD701, MMBD701L, SMMBD701L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	70	–	–	V
Total Capacitance ($V_R = 20 \text{ V}$, $f = 1.0 \text{ MHz}$) Figure 1	C_T	–	0.5	1.0	pF
Reverse Leakage ($V_R = 35 \text{ V}$) Figure 3	I_R	–	9.0	200	nA
Forward Voltage ($I_F = 1.0 \text{ mA}$) Figure 4	V_F	–	0.42	0.5	V
Forward Voltage ($I_F = 10 \text{ mA}$) Figure 4	V_F	–	0.7	1.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping†
MBD701G	TO-92 (Pb-Free)	1,000 Units / Bulk
MMBD701LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD701LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD701LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBD701, MMBD701L, SMMBD701L

TYPICAL ELECTRICAL CHARACTERISTICS

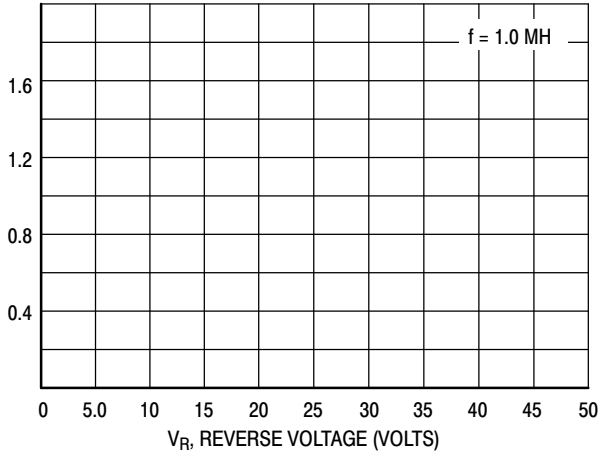


Figure 1. Total Capacitance

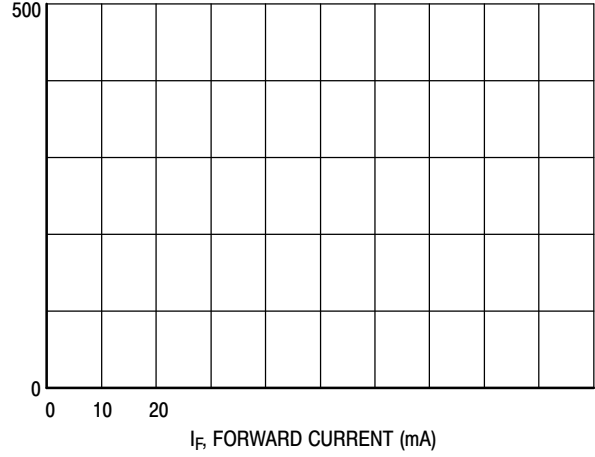


Figure 2. Minority Carrier Lifetime

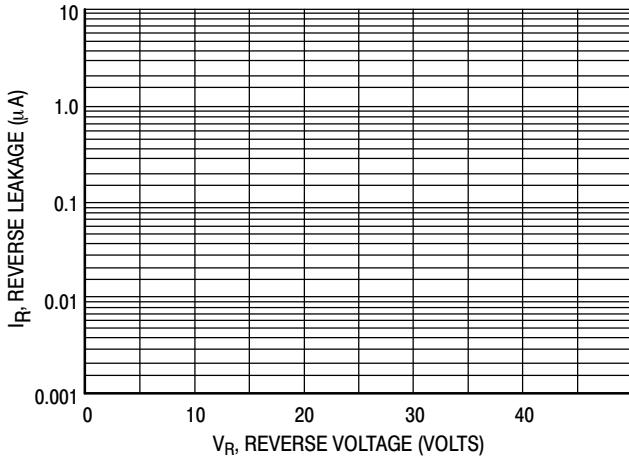


Figure 3. Reverse Leakage

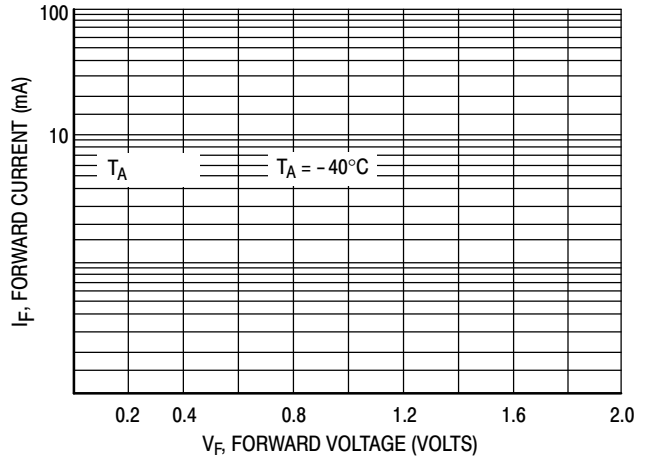
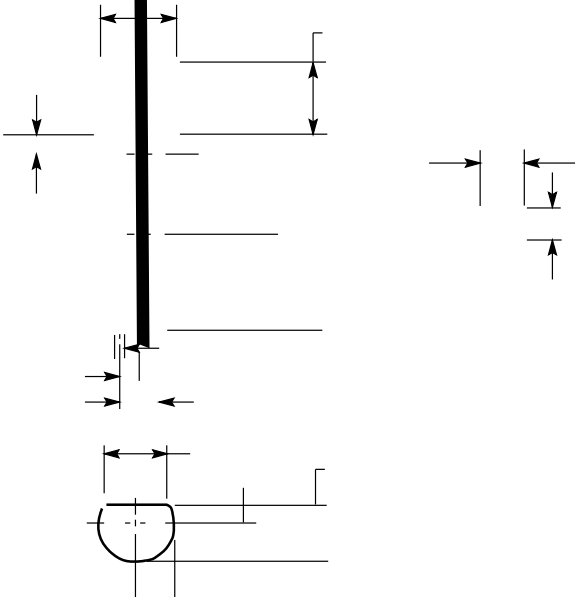
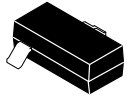


Figure 4. Forward Voltage

CASE 182-06





SCALE 4:1

SOT 23 (TO 236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

SOT 23 (TO 236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE
3.

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